

Complementary Silicon Plastic Power Transistors

... designed for use as high–frequency drivers in audio amplifiers.

• DC Current Gain Specified to 5.0 Amperes

$$h_{FE} = 50 \text{ (Min)} @ I_C = 0.5 \text{ Adc}$$

= 10 (Min) @ I_C = 2.0 Adc

• Collector-Emitter Sustaining Voltage —

$$V_{CEO(sus)} = 250 \text{ Vdc (Min)} - \text{MJE}15032, \text{MJE}15033$$

• High Current Gain — Bandwidth Product

$$f_T = 30 \text{ MHz (Min)} @ I_C = 500 \text{ mAdc}$$

• TO-220AB Compact Package

MAXIMUM RATINGS

Rating	Symbol	MJE15032 MJE15033	Unit
Collector–Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CB}	250	Vdc
Emitter–Base Voltage	V _{EB}	5.0	Vdc
Collector Current — Continuous — Peak	IC	8.0 16	Adc
Base Current	I _B	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	50 0.40	Watts W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

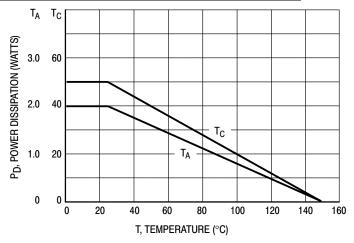


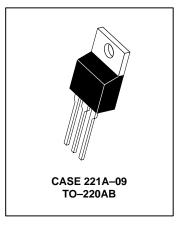
Figure 1. Power Derating

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

NPN MJE15032* PNP MJE15033*

*ON Semiconductor Preferred Device

8.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY
SILICON
250 VOLTS
50 WATTS



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I _C = 10 mAdc, I _B = 0)	MJE15032, MJE15033	V _{CEO(sus)}	250	_	Vdc
Collector Cutoff Current (V _{CB} = 150 Vdc, I _E = 0)	MJE15032, MJE15033	I _{CBO}	_	10	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		I _{EBO}	_	10	μAdc
ON CHARACTERISTICS (1)	ON CHARACTERISTICS (1)				
DC Current Gain $(I_C = 0.5 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 2.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$		h _{FE}	50 50 10	_ _ _ _	_
Collector–Emitter Saturation Voltage $(I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc})$		V _{CE(sat)}	_	0.5	Vdc
Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc)		V _{BE(on)}	_	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain — Bandwidth Product (2) (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)		f _T	30	_	MHz

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

⁽²⁾ $f_T = |h_{fe}| \cdot f_{test}$.

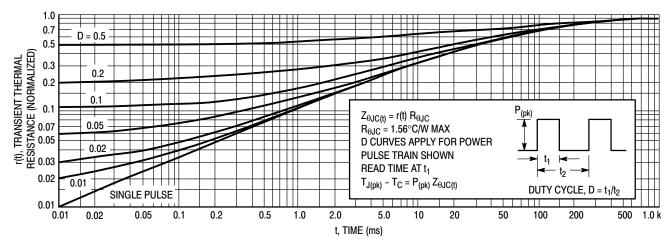


Figure 2. Thermal Response

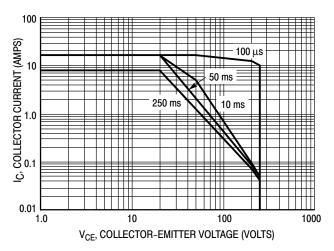


Figure 3. MJE15032 & MJE15033 Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figures 3 and 4 is based on $T_{J(pk)} = 150^{\circ} C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 2. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



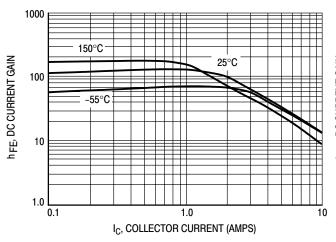


Figure 4. NPN — MJE15032 V_{CE} = 5 V DC Current Gain

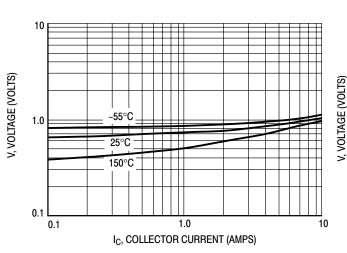


Figure 6. NPN — MJE15032 $V_{CE} = 5 V V_{BE(on)} Curve$

PNP — MJE15033

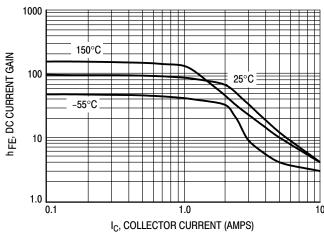


Figure 5. PNP — MJE15033 V_{CE} = 5 V DC Current Gain

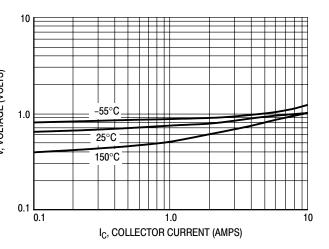
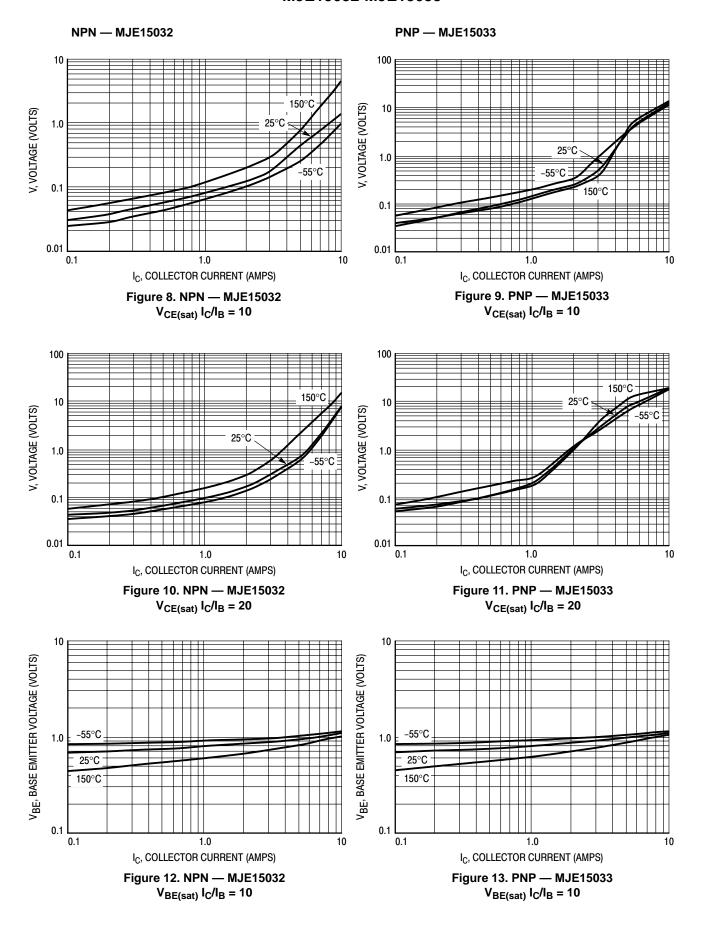
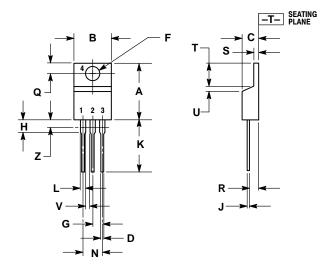


Figure 7. PNP — MJE15033 $V_{CE} = 5 V V_{BE(on)} Curve$



PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 **ISSUE AA**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04





ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303–308–7140 (Mon–Fri 2:30pm to 7:00pm CET)

Email: ONlit-german@hibbertco.com

French Phone: (+1) 303–308–7141 (Mon–Fri 2:00pm to 7:00pm CET)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303–308–7142 (Mon–Fri 12:00pm to 5:00pm GMT)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

Toll-Free from Mexico: Dial 01-800-288-2872 for Access -

then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 1-303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

Lilian. Ornit—asia@filobertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

Phone: 81–3–5740–2700 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.